UTC UNISONIC TECHNOLOGIES CO., LTD

8050S

NPN SILICON TRANSISTOR

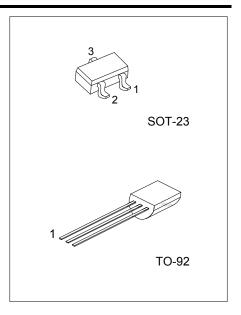
LOW VOLTAGE HIGH CURRENT SMALL SIGNAL NPN TRANSISTOR

DESCRIPTION

The UTC 8050S is a low voltage high current small signal NPN transistor, designed for Class B push-pull audio amplifier and general purpose applications.

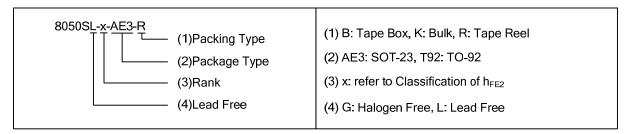
FEATURES

- *Collector current up to 700mA
- *Collector-Emitter voltage up to 20V
- *Complementary to UTC 8550S

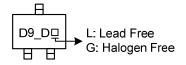


ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen-Free	Package	1	2	3	Packing	
8050SL-x-AE3-R	8050SG-x-AE3-R	SOT-23	E	В	С	Tape Reel	
8050SL-x-T92-B	8050SG-x-T92-B	TO-92	E	С	В	Tape Box	
8050SL-x-T92-K	8050SG-x-T92-K	TO-92	E	С	В	Bulk	
8050SL-x-T92-R	8050SG-x-T92-R	TO-92	Е	С	В	Tape Reel	



MARKING (For SOT-23 Package)



■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Base Voltage		V_{CBO}	30	V	
Collector-Emitter Voltage		V_{CEO}	20	V	
Emitter-Base Voltage		V_{EBO}	5	V	
Collector Current		Ic	700	mA	
Collector Dissipation(T _A =25°C)	SOT-23	P _C	350	mW	
	TO-92		1	W	
Junction Temperature		TJ	+150	°C	
Storage Temperature		T _{STG}	-40 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

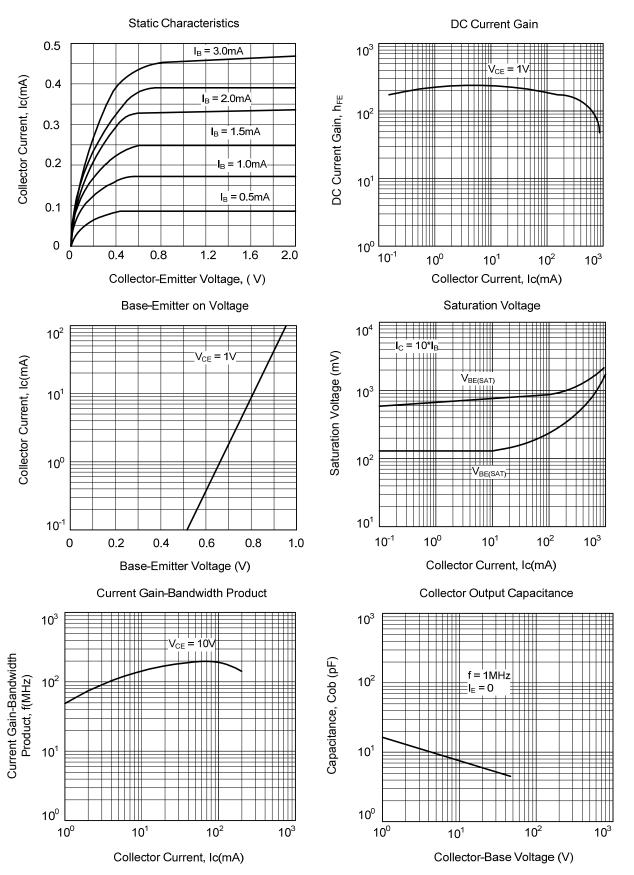
■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = 100 \mu A, I_E = 0$	30			V
Collector-Emitter Breakdown Voltage	BV_CEO	$I_{\rm C} = 1 {\rm mA}, I_{\rm B} = 0$	20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = 100 \mu A, I_C = 0$	5			V
Collector Cut-Off Current	I _{CBO}	$V_{CB} = 30V, I_{E} = 0$			1	uA
Emitter Cut-Off Current	I _{EBO}	$V_{EB} = 5V, I_{C} = 0$			100	nA
	h _{FE1}	$V_{CE} = 1V, I_C = 1mA$	100		400	
DC Current Gain(note)	h _{FE2}	$V_{CE} = 1V, I_{C} = 150 \text{ mA}$	120			
	h _{FE3}	$V_{CE} = 1V, I_{C} = 500mA$	40			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$			0.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$			1.2	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$V_{CE} = 1V, I_C = 10mA$			1.0	V
Current Gain Bandwidth Product	f _T	$V_{CE} = 10V, I_{C} = 50mA$	100			MHz
Output Capacitance	Cob	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$		9.0		pF

■ CLASSIFICATION OF h_{FE2}

RANK	С	D	E
RANGE	120-200	160-300	280-400

■ TYPICAL CHARACTERISTICS



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